

## Abstract

5       An interconnect for semiconductor components includes a  
substrate, and interconnect contacts on the substrate for  
electrically engaging component contacts on the components.  
The interconnect contacts include silicon carbide conductive  
layers, and conductors in electrical communication with the  
silicon carbide conductive layers.     The silicon carbide  
10   conductive layers provides a wear resistant surface, and  
improved heat transfer between the component contacts and the  
interconnect contacts.   The silicon carbide conductive layers  
can comprise doped silicon carbide, or alternately thermally  
oxidized silicon carbide.   The interconnect can be configured  
15   for use with a testing apparatus for testing discrete  
components such as dice or chip scale packages, or  
alternately for use with a testing apparatus for testing  
wafer sized components, such as wafers, panels and boards.  
In addition, the interconnect can be configured for  
20   constructing semiconductor packages and electronic assemblies  
such as multi chip modules.

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